Lattice therm al conductivity of disordered N iP d and N iP t alloys

A ftab A lam z and A bhijit M ookerjee y

SN.Bose NationalCentre for Basic Sciences, JD Block, Sector III, Salt Lake City, Kolkata 700098, India

A b stract. Numerical calculations of lattice therm al conductivity are reported for the binary alloys NiPd and NiPt. The present work is a continuation of an earlier paper by us [1] which had developed a theoretical fram ework for the calculation of con guration-averaged lattice therm al conductivity and therm al di usivity in disordered alloys. The form ulation was based on the augmented space theorem [2] combined with a scattering diagram technique. In this paper we shall show dependence of the lattice therm al conductivity on a series of variables like phonon frequency, temperature and alloy composition. The temperature dependence of (T) and its relation to the measured therm al conductivity is discussed. The concentration dependence of appears to justify the notion of a m inim um therm al conductivity as discussed by K ittel, Slack and others [3, 4]. W e also study the frequency and com position dependence of the therm al di usivity averaged over m odes. A num erical estim ate of this quantity gives an idea about the location ofm obility edge and the fraction of states in the frequency spectrum which is delocalized.

PACS num bers: 72.15.Eb, 66.30.X j, 63.50.+ x

1. Introduction

Lattice therm al conductivity of substitutionally disordered alloys yield valuable inform ation about the interactions of therm al excitations, phonons, with composition uctuations on their crystal lattice. Over the past few years num erous experimental studies [5]-[8] of the therm al conductivity of disordered alloys have provided considerable insight into the nature of their elementary excitations.

The theory of lattice them al conductivity for perfect crystals and ordered alloys has been set up on a rigorous basis. How ever the same is not true for disordered alloys. The presence of disorder results in scattering that not only depends on the impurity concentration but also crucially on both the relative masses and size di erence between the constituent atom s. For large mass or size di erences, the elect of disorder can be quite unusual. Because of this, detailed comparison between theory and experiment on the basis of realistic models has not been very extensive. Model calculations are

z E-mail: alam@bose.res.in

y E-m ail: abhijit@ bose.res.in

m ostly based on m ean-eld approaches with diagonal disorder alone. W hereas in phonon problem s essential o -diagonal disorder in the force constants cannot be dealt within single site m ean eld approximations. Such disorder e ects cannot be ignored in realistic calculations.

W hen we come to comparison with experiment, however, we face a dierent kind of di culty. In any experiment, the measured therm al conductivity consists of the sum of an electronic component $_{e}$ and a lattice component $_{L}$ and $= _{e}$ + Τ. • Assuming the therm al analogue of M atthiessen's rule to be valid, the electronic therm all resistivity $W_e = 1 = e$ is given by the sum of an ideal resistivity and an in purity or residual term . It is often assumed that the ideal resistivity remains unaltered by alloying and can be obtained from the measurem ents on pure metals. The residual resistivity W $_{\rm r}$ can be calculated with the help of W idem ann-Franz law $W_r = 0$ (T)=(L₀T), where L₀ is the Lorenz number and 0 (T) is determined by m easuring the electrical resistivity of the alloy at several tem peratures. The lattice component $_{\rm L}$ can then be separated out from the observed conductivity . Overall what we would like to convey from these details is that a direct measurem ent of the lattice component of the therm al conductivity is not feasible. There always exists certain assumptions behind the calculation of e and hence it is not possible always to obtain reliable estimates for this quantity which consequently a ects the separation of $_{\rm L}$ from the observed conductivity .

In an earlier communication [1] (hereafter referred to as AM) we had developed a form alism for the calculation of conguration averaged lattice therm alconductivity and therm aldiusivity for a disordered binary alloy. Unlike single-site mean-eld approaches, this form ulation has no restrictions on what kind of substitutional disorder can be studied. It explicitly takes into account uctuations in masses, force constants and heat currents between di erent nuclei. It also maintains, on the average, the sum rule between the diagonal and o -diagonal parts of the dynamical matrix which elim inates the translationalm ode. We had shown that the dom inant e ect of disorder is to renorm alize each propagator as well as the current term s in the K ubo form ula.

The purpose of this article is to implement the formulation (AM) for a detailed num erical study of the con guration averaged lattice conductivity and them al di usivity for disordered NiPt and NiPd alloys. The choice of the alloy systems is not arbitrary. We have chosen these alloys in order to propose a system atic study of the e ects of m ass disorder and strong force constant disorder. In the NiPd alloys, m ass disorder is much larger than the force constant disorder. How ever both kinds of disorder dom inate in the N iP t alloys. Moreover in both the two alloy system s there is a large size m ism atch between the constituents. This indicates that the standard single site mean eld theories would be inadequate to capture these e ects. These alloy system s are therefore ideal for the illustration of the advantages of the augmented space block recursion method proposed by us [9]. Theoretically there have been many attempts [10]-[13] to develop an adequate approximation for understanding the lattice them al conductivity of metals and alloys. The majority were based on model calculations either for perfect crystals or ordered alloys. One of the most successfulm ean-eld approxim ation was the coherent potential approxim ation (CPA) [14] in combination with the appropriate Kubo formula. The CPA is a single site m ean-eld theory capable of dealing only with m ass disorder. There have been m any attem pts to generalize the CPA in order to treat both o -diagonal and environm ental

disorder. In many cases these approximations did not satisfy the necessary hergibtz analytic and lattice translational invariance properties of the conguration averaged G reen functions. Two very similar approaches, both based on the augmented space theorem, have been recently proposed : the itinerant cluster CPA (ICPA) [15] and the augmented space recursion [16]. These have been used to study the lattice dynamics of N $i_{55}Pd_{45}$, N $i_{50}Pt_{50}$ and N $i_{88}Cr_{12}$ alloys. In a more generalized context of inelastic neutron scattering in disordered alloys, an augmented space block recursion (A SBR) has also been proposed recently [9]. The A SBR calculates the full G reen and Self-energy matrices instead of their diagonal entries alone. These are required for obtaining the response functions.

In this paper, we shall make use of the ASBR technique to implement the theoretical formulation for the lattice thermal conductivity developed earlier by us. W e shall study the dependence of lattice thermal conductivity on phonon frequency as well as on temperature in a series of disordered N iPd and N iPt alloys covering the full range of alloy compositions.

As far as the tem perature dependence of lattice conductivity is concerned, our results follow a general trend. We shall also discuss how the lattice conductivity behave as a function of concentration at several xed tem peratures. The notion of a m inim um therm alconductivity willbe justi ed. It willbe shown that low tem perature resonant m odes considerably decrease the conductivity. An idea about the location of the m obility edge will be discussed from the phonon-frequency dependence of the m ode averaged harm onic di usivity. This dependence also gives a rough idea about what fraction of the states across the frequency spectrum are delocalized and therefore can carry current. The concentration dependence of the harm onic di usivity will also be displayed.

2. Theoretical form ulation

In the next two subsections, we shall apply the form alism introduced in our earlier paper (AM) to study N iPd and N iPt alloys across the alloy composition range. In (AM) we have discussed the theoretical form alism in great detail. We shall present only the main pointshere and leave the reader to refer to (AM) for greater detail.

The derivation of a K ubo form ula for therm alconductivity requires an additional statistical hypothesis, which states that a system in steady state has a space dependent local tem perature T $(r_i) = [B_B(r_i)]^{-1}$. The matrix element of the heat current in the basis of the eigenfunctions of the Ham iltonian is given by :

$$S_{0}(k) = \frac{h}{2} + k + k \circ v_{0}(k);$$

where, the phonon group velocity $v \circ (k)$ is given by

$$v_{0} = \frac{1}{2^{p} \frac{X X}{k k^{0}}}$$
 (k) $r_{k}D$ (k) $_{0}$ (k)

here ; ⁰ label the various modes of vibration, $_{k}$; $_{k}$ · are their frequencies,

(k); $_{\circ}$ (k) are the polarization vectors and D (k) is the Fourier transform of mass scaled dynam ical matrix.

W e shall consider the case where the temperature gradient is uniform within the system. The Kubo formula then relates the linear heat current response to the temperature gradient eld

hS (t) i =
$$\begin{bmatrix} X & Z_{1} \\ dt^{0} & (t & t^{0}) r & T(t); \end{bmatrix}$$

where

$$() = () \frac{1}{T} \int_{0}^{Z} dhS (ih);S()i;$$

() is the H eaviside step function, and

$$S(ih) = e^{H} S e^{H}$$
:

h i on the right-hand side of the above equation denotes therm allaveraging over states in the absence of the tem perature gradient. The above equation can be rewritten in the form of a K ubo-G reenwood expression

$$(;T) = _{I} (;T) + _{II} (;T)$$

$$I_{I}(;T) = \frac{Z}{T} \frac{d^{3}k}{8^{3}} X X \frac{hn_{k} \circ i hn_{k} i}{h(k + k^{\circ})} S_{0}(k) S_{0}(k) (k + k^{\circ})$$

$$II (;T) = \frac{1}{B^{T^{2}}} \begin{pmatrix} Z & \frac{d^{3}k}{8^{3}} & M_{k} \text{ is } (k) \\ B & T & \frac{d^{3}k}{8^{3}} & \frac{X}{6^{2}(h_{k})} & \frac{d^{3}k}{8^{3}} & M_{k} \text{ is } (k) \\ \end{pmatrix} \begin{pmatrix} Z & 0 \\ \frac{d^{3}k}{8^{3}} & M_{k} \text{ is } (k) \\ & \# \\ \end{pmatrix} \begin{pmatrix} H \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Q \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H \end{pmatrix} \end{pmatrix} \begin{pmatrix} Z \\ H$$

where $h_k i = (e^{h_k} 1)^1$ is the equilibrium Bose E instein distribution function and T is the absolute temperature.

The rst expression is for inter-band transitions, while the second expression is for intra-band transitions. For an isotropic response, we can rewrite the rst expression as

$$I(;T) = \frac{X}{3T} \begin{bmatrix} X & Z & Z \\ d & 0 \end{bmatrix} \begin{bmatrix} d^{3}k & X \\ 8 & 3 \end{bmatrix} \begin{bmatrix} 0 & (k;T) & (k;T) & (k, 0) \end{bmatrix} \begin{bmatrix} 0 & (k, 0) & (k, 0) \end{bmatrix} \begin{bmatrix} 0 & (k, 0) & (k, 0) & (k, 0) \end{bmatrix} \begin{bmatrix} 0 & (k, 0) & (k, 0)$$

where

$$\dot{B}_{0}(k;T) = \frac{s}{\frac{hn_{k}\circ i}{h(k - k}} S_{0}(k):$$

(1)

Lattice therm al conductivity of disordered N iP d and N iP t alloys

W e m ay rew rite the above equation as

$$I(;T) = \frac{1}{3T} X^{2} d^{0} \frac{d^{3}k}{8^{3}} Tr^{h} (k;T) = m fG(k;^{0})g^{h}(k;T) = m fG(k;^{0}+)g^{h}(k;T)$$

The operator G () is the phonon G reen operator $(M^{2}I)^{1}$. The Trace is invariant in di erent representations. For crystalline systems, usually the B loch basis fk; ig is used. For disordered systems, prior to con guration averaging, it is more convenient to use the basis fk; ig, where k is the reciprocal vector and represents the coordinate axes directions. We can transform from the mode basis to the coordinate basis by using the transform ation matrices (k) = (k). For example

$$\hat{B} (k;T) = T(k) \hat{B} (k;T) \hat{C}(k):$$

Ifwede ne

$$(z_1;z_2) = \frac{Z}{8} \frac{d^3k}{8^3} \operatorname{Tr}^{h} \mathcal{B} G (k;z_1) \mathcal{B} G (k;z_2)^{i}: \qquad (3)$$

then the above equation becom es,

$$(;T) = \frac{1}{12 T} X^{2} d^{0} (^{0}; ^{0+} +) + (^{0+}; ^{0} +)$$

$$(^{0+}; ^{0+} +) (^{0}; ^{0} +)$$

$$(^{0}; ^{0+} +) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+} +)) (^{0+}; ^{0+}$$

where

$$f(^{+}) = \lim_{i \to 0} f(+i); f() = \lim_{i \to 0} f() i);$$

W e have used the herglotz analytic property [16] of the G reen operator

$$G(+i) = \langle e G()$$
 isgn() = m $G()$:

For disordered m aterials, we shall be interested in obtaining the con guration averaged response functions. This will require the con guration averaging of quantities like $(z_1;z_2)$. This averaging procedure we have discussed in detail in (AM):

$$(z_1; z_2) = (1) (z_1; z_2) + (z_1; z_2)^{\text{ladder}}$$
(5)

The rst term in the right hand side stands for the disorder induced corrections where the disorder scattering renorm alizes the phonon propagators as well as the heat currents. In this term, corrections to the heat current is related to the self-energy of the propagators. The second term of Eq. (5) includes the vertex corrections due to the correlated propagation.

Lattice therm al conductivity of disordered N iPd and N iPt albys

For a harm onic solid, a tem perature independent mode di usivity D is de ned as

$$D (k) = \frac{X}{\frac{1}{2}} S_{0}(k) S_{0}(k) (k) (k) (k) (k)$$

This is an intrinsic property of the -th norm alm ode and provides an unambiguous criterion for localization.

The averaged therm aldiusivity (averaged overmodes) is then given by

$$D () = \frac{\frac{d^{3}k}{8^{3}} D (k) (k)}{\frac{Z}{8^{3}} (k)} = \frac{Z}{\frac{d^{3}k}{8^{3}} (k)} = \frac{Z}{\frac{d^{3}k}{8$$

Assuming isotropy of the response, we can rewrite the numerator of above equation as

$$D_{tot}() = d_{0}^{2} \frac{d^{3}k}{8^{3}} \sum_{0}^{3} b_{0}(k) b_{0}(k) (0_{k^{0}}) (k^{0}) (k^{0$$

where

$$\oint _{0} (k) = \frac{1}{k} S_{0} (k):$$

W e m ay again rew rite the above equation for D _{tot} as D_{tot}() = $\frac{1}{2}$ d⁰ $\frac{d^3k}{8^3}$ Tr = m fG (k; ⁰)g^b (k)=m fG (k; ⁰)g^b (k)=m fG (k;)gⁱ

The averaged thermal diusivity can then be expressed as (for an isotropic response)

$$D() = \frac{1}{3}^{X} D() = \frac{1}{3}^{Z} \frac{D_{tot}()}{\frac{d^{3}k}{8^{-3}}} \text{Tr} \models m \text{ fG } (k;)g]$$
(6)

For disordered m aterial, we shall be interested as before in obtaining the con guration averaged therm aldiusivity. The con guration averaged therm aldiusivity can be expressed (to a 1st order approximation) in the form

D

$$D() = \frac{1}{3} \frac{D_{tot}()}{\frac{d^{3}k}{8^{3}} \text{Tr} \models m \quad G(k;)]};$$
(7)

where

Lattice therm al conductivity of disordered N iP d and N iP t albys

3. RESULTS AND DISCUSSION

The details of num erical calculation for the two alloys of our interest in the present work are as follows:

W e have carried out calculations on 501 -points.

A small in aginary part of the frequency = 0.001 has been used for evaluating the G reen m atrix and Self-energy m atrix in the augmented space block recursion [9].

The calculation of lattice conductivity has been done at 40 tem peratures.

For the Brillouin zone integration, 145 k-points in the irreducible 1=48-th of the zone produced well converged results.

3.1. N iPd alby : Strong m ass and weak force constant disorder.

For a list of general properties of fcc N i and Pd, we refer the reader to Ref. [16]. This particular alloy has already been studied experim entally by Farrell and G reig [5] using conventional potentiom etric techniques. But unfortunately their investigation was limited only to very dilute alloys in the tem perature range 2-100 K. In an earlier communication (AM) we have already shown a comparison of our results for the tem perature dependence of therm al conductivity with theirs for a dilute N $i_{99}Pd_{01}$ alloy.

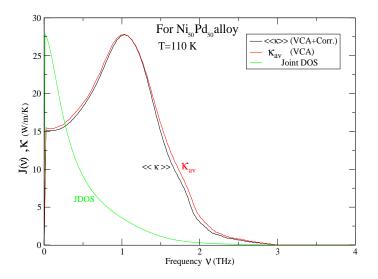
Our initial focus in the earlier communication [1] was to calculate the e ect of disorder scattering over an averaged medium. We had made use of the multiple scattering diagram technique and went beyond the framework of CPA which treats only diagonal disorder. Rather we had applied the technique in a more generalized context with the inclusion of diagonal as well as o -diagonal disorder arising out of the disorder in the dynam icalm atrix. In an attempt to compare the e ect of averaged heat current and disorder induced renorm alized heat current on the lattice therm al conductivity, we have plotted Fig. 1.

Fig 1 shows the results for disordered N i_{50} P d₅₀ alby. The black curve represents the lattice conductivity including all kinds of disorder induced corrections : e.g. corrections to the heat current and the vertex corrections, while the red curve stands for the sam e quantity but using averaged heat currects and w ithout vertex corrections. The green curve in this gure shows the scaled joint density of states. From the gure it is clear that the transition rate `' is strongly dependent both on the initial and the nal energies throughout the phonon frequency (). That is

where J() is the joint density of states given by

$$J() = d^{0} \frac{d^{3}k}{8^{3}} \operatorname{Tr} = m \quad G(k; ^{0}) = m \quad G(k; ^{0}+)$$
(9)

Figure 1 shows that, the e ect of disorder corrections to the current term s on the overall shape of lattice conductivity is rather sm all in the N $i_{50}P d_{50}$ alloy. We should note that the e ect of disorder corrections to current and the vertex corrections in



F igure 1. (C olor O nline) C on guration averaged lattice them al conductivity vs phonon frequency (T H z) for N i₅₀P d₅₀ disordered alloy. The red line and black line shows the conductivity using the average VCA current and e ective current (consisting of average VCA current + disorder corrections + vertex correction) respectively. The green line in indicates the con guration averaged joint density of states.

these alloys become negligible beyond phonon frequencies ' 2.5 THz. For the higher frequency modes the e ect of scattering phenomenon is well described by the mean led approximation. It is in the low frequency region that con guration uctuation e ects beyond the mean-eld becomes signi cant.

There is a very in portant feature in Fig. 1 that still needs discussion : which is how to explain the origin of a dip in () at the lowest energy = 0? A similar kind of dip has also been reported by Feldm an et.al. [17] while studying am orphous Si and Si_{1x}Ge_x alloys. Their () have a small Lorenzian shaped dip centred at = 0. This rejects the missing intraband conductivity ^{II}. This dip in () stands at a smallbut nite value ['0]. The niteness of the dip in () is because of the fact that their calculation was based on a K ubo-G reenwood expression for the therm al conductivity with the delta functions in the expression broadened into a Lorenzian of sm all (but nite) width. However in our case it is evident from the Fig. 1 that this dip in () stands at ()! 0 at = 0. This is due to the simple reason that in our calculation the Lorenzian broadening has not been put in by hand, but it arises autom atically from the disorder e ect on the crystalline spectral function =m [G (k;)]. Another reason for this di erence in the position of dip in () may be due to the fact that Feldm an et.al. carried out their calculation at a xed wavevector k, while we have sum med over the entire B rillouin zone.

The origin of this dip can also be explained by looking at the joint density of states (JD O S) represented by green line in Fig. 1. This quantity has a dip near = 0 rem iniscent of the dip in the () curves. This indicates that a sm ooth convolution

of two G reen matrices G (k; ⁰) and G (k; ⁰+) (or two smooth densities of states obtained after sum ming k over the Brillouin zone), as appeared in the expression (5) of [1], is mainly responsible for such a sharp dip in the lattice conductivity at = 0. A sdiscussed by Feldmanetal, this dip at = 0 disappears as the system size N ! 1. They have also suggested an appropriate method to eliminate this dip in a sensible manner, which allows us to extrapolate the () curve from a value at > 0 ('0) to a value at = 0. This extrapolated value of () at = 0 is nothing but the d.c. value of the lattice thermal conductivity $_0$. In an attempt to calculate ($_0$), we have obtained a value of 15.25 W /m/K for N i_{50} P d_{50} alloy at T = 110 K.

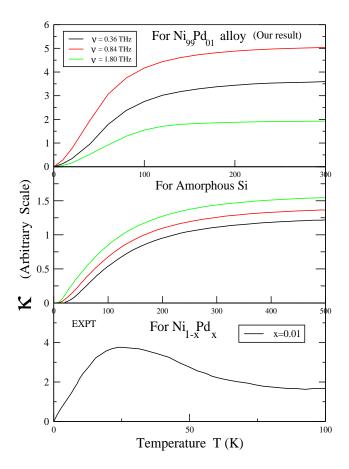
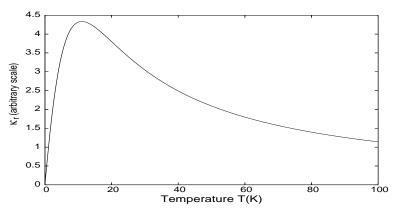


Figure 2. (Color Online) Therm al conductivity vs tem perature T (K) for N iPd alloys and Am orphous Si. The top panel shows our results on the lattice conductivity for N i₉₉Pd₀₁ alloy at three di erent frequency cut-o . The m iddle panel shows the lattice conductivity for am orphous Si [17] at three di erent cut-o frequency, while the panel at the bottom shows the experimental data [5] for the total therm al conductivity (= lattice + electronic contribution) of the same N i₉₉Pd₀₁ alloy.

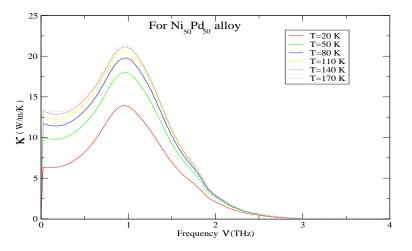
D irect comparison with the experimental data on these systems is dicult, because the experimental therm alconductivity also has a component arising out of



F igure 3. Residual or im purity contribution of the electronic part of the therm al conductivity

the contribution from electrons. Figure 2 shows the tem perature dependence of lattice conductivity. The top panel shows our theoretical result for the N $i_{99}P d_{01}$ alloy at three di erent frequencies. The bottom panel shows the experim ental data [5] on the total (electronic and lattice) therm al conductivity of the same 99-01 N iP d alloy. Since the frequency is not mentioned in the experimental data, we assume that it must be for low frequencies. The best comparison then will be between the middle (black) curve on the top panel and that in the bottom one. The two agree qualitatively, except at low tem peratures where we expect the electronic contribution to dom inate. In order to understand whether the deviation does arise from the electronic contribution, we have compared the top panel with the therm al conductivity of am orphous-Si [17], shown in the middle panel. In a-Sithe electrons near the Ferm i level are localized and hence cannot carry any current. The contribution to therm al conductivity arises from scattering due to con guration uctuations in the am orphous material. Qualitatively we expect the results to be similar to con guration uctuation scattering in random alloys. A lm ost the entire contribution should com e from the phonons. The behaviour of the two panels are quite similar. The origin of the hump in the experimental lattice conductivity can also be understood if we assume W idem ann-Franz law and write the residual part of the electronic contribution of the therm al resistivity as $r = L_0 T = 0$ (T). Here L_0 is the Lorenz number and 0 (T) is the electrical resistivity. Assuming that the electrical resistivity behaves as $_0$ (T) = A + BT + CT² at low tem peratures and with a suitable choice of the parameters, this contribution does show a hum p followed by a decreasing behaviour attening out at larger tem peratures (see Fig 3). The sum of the contribution shown in the top panel of Fig 2 and that in Fig 3 would lead to the experimental behaviour shown in the bottom panel of Fig 2. This is a plausibility argument and needs to be con med by a detailed calculation of the electronic contribution to the therm al conductivity.

W e shall now present the dependence of lattice them al conductivity and them al di usivity on parameters such as phonon frequency (), concentration (x) etc. In Fig. 4, we display the frequency dependence of lattice conductivity for N i_{50} P d_{50} alloy at various temperatures evaluated using Eq. 5. The gure clearly shows the saturation of lattice conductivity as we proceed towards the higher temperatures. The d.c. value of the conductivity (), which is just extrapolation of () curve from a value at



F igure 4. (C olor O nline) The conguration averaged lattice therm alconductivity vs phonon frequency (T H z) at di erent tem peratures T for N i_{50} P d₅₀ alloy.

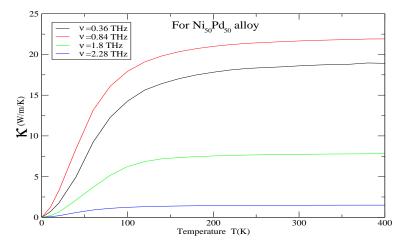
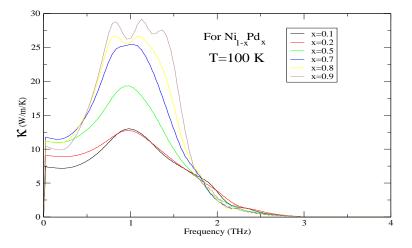


Figure 5. (Color Online) The averaged lattice thermal conductivity vs temperature T (K) at various cut-o frequencies $_{\rm cutoff}$ for N $i_{50}P\,d_{50}$ alloy.

> 0 to a value at = 0, increases as we increase the tem perature.

The temperature dependence of lattice therm al conductivity for the N i_{50} P d_{50} alloy at various phonon frequencies are shown in Fig. 5. It is qualitatively similar to N i_{50} P t_{50} alloy. The conductivity initially increases with temperature rejecting a quadratic T-dependence (in the low T-regim e) and ultimately reaches a T-independent saturated value (at higher temperatures).

Figure 6 shows the lattice conductivity as a function of frequency at T = 100 K



F igure 6. (C olor O nline) F requency dependence of lattice therm al conductivity for various alloys N i_{1 x} P d_x at T = 100 K .

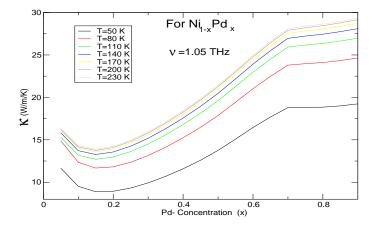
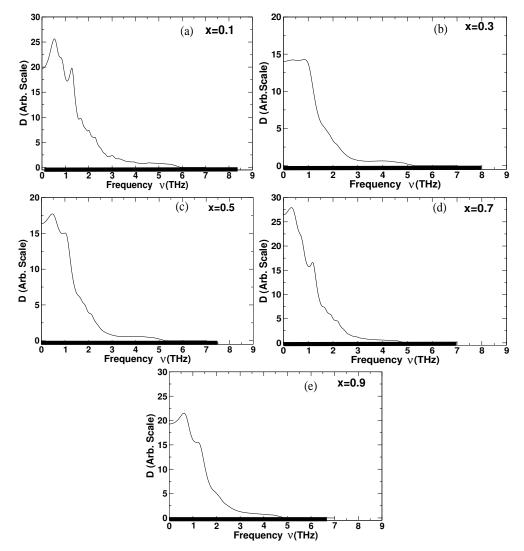


Figure 7. (Color Online) Lattice thermal conductivity vs Pd-concentration for various temperature T at phonon frequency = 1.05TH z.

for various alloy com positions. C om paring the results of F ig. 6 with those of F ig. 14 for N iPt, it is clear at a glance that the overall shape of frequency dependence of for various alloys of N i₁ $_x$ Pd_x boks sim ilar, how ever for x= 0.8 and x= 0.9 extra structure appears in the frequency dependence. Sim ilar behaviour has also been observed for x= 0.9 in N i₁ $_x$ Pt_x alloy in F ig. 14. We believe that this behaviour for N i₁ $_x$ Pd_x alloy at x= 0.8 and 0.9 m ay be due to the strong disorder in m asses, the e ect of which becomes important in the two dilute lim it alloys. Such an anom alous behaviour is also rejected in the concentration dependence of lattice conductivity. This is shown in F ig. 7, which plots the lattice conductivity vs Pd-concentration (x) at a xed frequency = 1.05 T H z for various tem peratures.



F igure 8. The con guration averaged therm aldi usivities D () for N i₁ $_xP\,d_x$ alloys. (a) x= 0.1; (b) x= 0.3; (c) x= 0.5; (d) x= 0.7; (e) x= 0.9.The broad line on the frequency axis shows the extent of the vibrational spectrum .

The therm aldi usivities D () are in portant because the elect of disorder is often manifested in them more directly than in the conductivities. Not only that therm al di usivity also gives an approximate idea about the location of mobility edge as well as the fraction of delocalized states. In Fig. 8 we display the therm aldi usivity D () vs frequency for various compositions. The extent of the phonon frequency spectrum is shown by the broad lines. The density of states is non-zero across this spectrum range. The rst thing to note is that, the region of large di usivity in the ve sets of alloys at the higher frequency side is not the same. In other words the weakly de ned hum p in the lower as well as higher frequency side are located at di erent positions for di erent alloys. The low frequency maximum in di usivity is a minimum around the 50-50

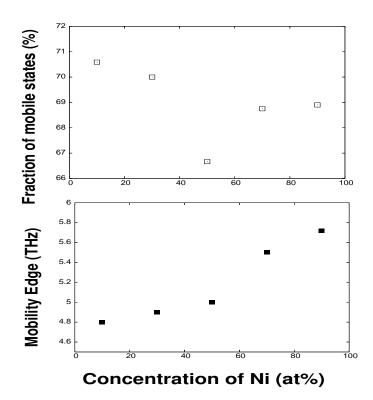


Figure 9. The position of the mobility edge (bottom) and the percentage of mobile phonon states (top) as a function of the alloy composition for N iPd alloy.

com position where the disorder scattering is the maximum. Above 2.8 THz, there is a smooth decrease of di usivity approximately linear in frequency D()/($_{\rm c}$), with the critical exponent '1 and a critical frequency $_{\rm c}$ where D() vanishes to within a very small level of noise. The allowed phonon states beyond this frequency must be due to localized phonon modes. The critical frequency $_{\rm c}$ locates the mobility edge above which the di usivity is strictly zero in the in nite size limit. Once the mobility edge is located, the fraction of de-localized states may be estimated directly. It is clear from the gure that location of mobility edge varies with composition. Consequently the percentage of de-localized states available for therm al conduction in the system also varies with composition. An inspection of Fig. 8 determ ines the location of the mobility edges ($_{\rm c}$) for the we di erent compositions. The following gure 9 which shows the position of the mobility edge and the percentage of mobile phonon states in the spectrum as a function of the composition is quite illustrative.

The maximum percentage of localized states occur at 50-50 composition where we expect disorder scattering to be a maximum. The mobility edge moves to higher frequencies as the concentration of N i increases, but so does the band width of the phonon spectrum. The minimum percentage of mobile phonon states available for therm al conduction occurs, as expected, at around the 50-50 composition. A similar behaviour has also been discussed by Feldman et.al [17] while studying the elects of mass disorder on various Si_{H x}G e_x alloys.

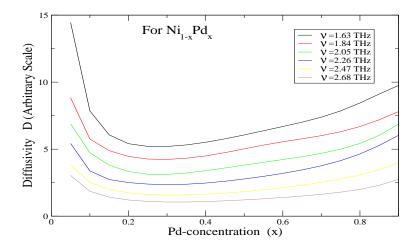


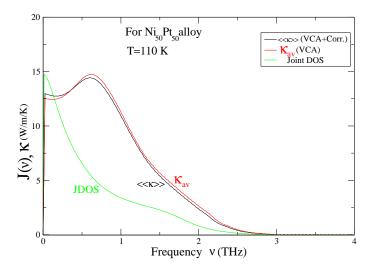
Figure 10. (Color Online) The averaged thermal diusivity D () vs Pd-concentration at various cut-o frequencies $_{\rm cutoff}$ for N i_ xPd_x alloy.

Figure 10 shows the concentration dependence of therm aldi usivity for N $i_1 _x P d_x$ alloy at various frequencies (). As expected from our earlier discussion, the m inum um di usivity occurs around the 50–50 composition, where disorder scattering is maximum. The curves have asymmetry around x = 0.5 which decreases with increasing frequency. This asymmetry relects a similar asymmetry in the therm al conductivity as a function of composition.

3.2. NiPt alloy: Strong m ass and force constant disorder.

W e refer the reader to a previous article [16] by us for som e of the basic properties of fcc N i and Pt which is relevant for our present calculation. It has been our experience [16, 9] that the e ect of disorder in N iPt alloy is more dram atic than N iPd. For instance the appearance of sharp discontinuities observed in the dispersion where we have resonance states and consequent increase in the line-width [16].

Figure 11 shows the results for disordered N $i_{50}P t_{50}$ alloy. As before, the black curve represents the lattice conductivity including all kinds of disorder induced corrections : e.g. corrections to the heat current and the vertex corrections, while the red curve stands for the same quantity but using averaged heat currents and w ithout vertex corrections. The green curve shows the scaled joint density of states. From the gure it is clear that as in the case of N iP d, the transition rate ' ' is strongly dependent both on the initial and the nale nergies throughout the phonon frequency (). Figure 11 also clari es that although the e ect of disorder corrections to the current term s is sm all, but this e ect is comparatively m ore pronounced in N $i_{50}P t_{50}$ than in N $i_{50}P d_{50}$. The e ect of disorder corrections to current and the vertex corrections in the present case become negligible beyond phonon frequencies ' 2.4 THz. In the low frequency region, con guration uctuation e ects beyond the mean eld is more pronounced in N iP d. Thism ay be because of the two simple physical reasons : First, the



F igure 11. (ColorOncurve) Con guration averaged lattice them alconductivity vs phonon frequency (THz) for N i_{50} Pt $_{50}$ disordered alloy. The red curve and black curve shows the conductivity using the average VCA current and e ective current (consisting of average VCA current + disorder corrections+ vertex correction) respectively. The green curve indicates the con guration averaged joint density of states.

N iPt is an alloy where both m ass $(m_{Pt}/m_{Ni}' 3)$ as well as force constant (Pt-force constants are on an average 55% larger than those of N i) disorder dom inates, while in N iPd alloy the m ass disorder $(m_{Pd}/m_{Ni}' 1.812)$ is weaker than N iPt and the force constants are almost the same for the two constituents. Second, from a purely phenom enological point of view, there is a larger size m ism atch between N i and Pt in N iPt alloy as com pared to N i and Pd in N iPd alloy.

In Fig. 12 we display the frequency dependence of lattice therm al conductivity for N i_{50} P t_{50} alloy at various tem peratures, evaluated using the form ulae given in Eq. (3) and (5). We note from Fig. 12 that as we increase the tem perature, the di erence in lattice conductivity at a particular frequency is quite large in the lower tem perature regime (20 T 80K), how ever the di erence starts to saturate as we go to higher tem peratures. As discussed in the previous section, the extrapolated value of () curve from a value at > 0 (next to = 0) to a value at = 0 is called the d.c. value of lattice therm al conductivity ($_0$). Figure 12 clearly shows that this d.c. value of the conductivity increases as we go on to increase the tem perature. This is expected because in the d.c. lim it the mechanism of heat conduction is transfer of energy between delocalized modes of equal energy by the heat current operator.

The behaviour of () vs curve in both N Pd and N Pt is qualitatively similar, but there are some quantitatively dierent features. The maximum in N Pt is located at a lower frequency as compared with N Pd. A loo the overall magnitude of lattice conductivity in N Pd is higher than N Pt.

The tem perature dependence of lattice conductivity for N i_{50} P t_{50} alloy at various cut-o frequencies are shown in Fig. 13. The conductivity increases initially (in the

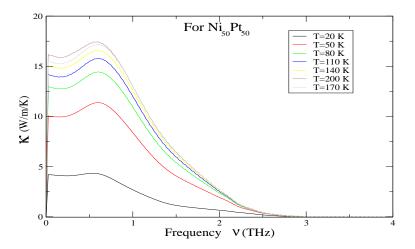


Figure 12. (Color Online) The conguration averaged lattice thermal conductivity vs phonon frequency (THz) at di erent temperatures T for N $i_{50}\,P\,t_{50}$ alloy.

low T-regime) as an approximate quadratic function of tem perature and ultimately increases smoothly to a T-independent saturated value. As far as such dependence of (T) in the high tem perature regime is concerned, the heat in this conduction channel

(1) In the high tem perature regime is concerned, the heat in this conduction channel is carried by non-propagating modes which are strongly in uenced by the disorder but mostly not localized and therefore able to conduct by intrinsic harm onic di usion. This is a smooth dependence which closely resembles the speci c heat and saturates like the speci c heat at high tem peraturs. Following Slack [4] we could call this piece the \minimum therm al conductivity". A number of authors have discussed that low

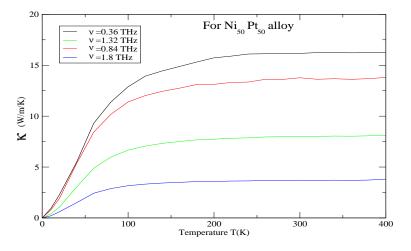
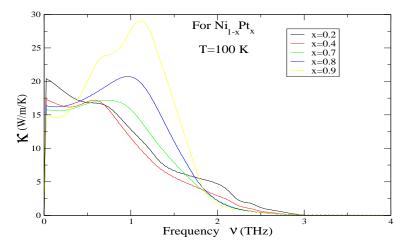


Figure 13. (Color Online) The averaged lattice thermal conductivity vs temperature T (K) at various cut-o frequency $_{\rm cutoff}$ for N $\rm i_{50}P\,t_{50}$ alloy.

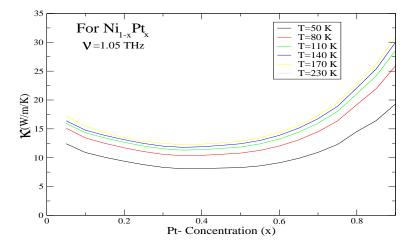


F igure 14. (C olor O nline) Frequency dependence of lattice therm alconductivity for various alloys N i $_{\rm X}$ Ptx at T = 100 K .

tem perature dependence of (T) shows a mild plateau like region. In this regime the heat is mainly carried by the propagating long wavelength acoustic modes. The complex inelastic scattering processes then kill of the low frequency contribution at higher temperatures leaving a peak which becomes the plateau. However there are situations, where the propagating modes become reasonably well damped (as in our calculation) and are no longerable to carry much heat. In such cases the contribution of delocalized and poorly conducting vibrations takes over, giving a net result in good accord with the Kittel's old idea. Under these circum stances the plateau like region in the low temperature regime alm ost disappears. The damping of propagating modes is also amplied as we make the alloy more and more concentrated. This can easily be veried by looking at the results of reference [5], which shows that as we increase the concentration the plateau like region goes down and gets smoother.

In Fig. 14, we display the frequency dependence of lattice conductivity for N iPt alloys at various compositions, but at a xed temperature T = 100 K. As before each of the curves have a dip at the lowest frequency. It is important to notice that as we increase the Pt-concentration x, structure appears in the behaviour of (). This indicates that the structure arises due to the contribution of Pt-atom (with largem ass) in the alloy.

The concentration dependence of lattice conductivity at a xed phonon frequency = 1.05T H z are plotted in Fig. 15. The various curves in this gure stand for various values of the tem perature T starting from a low ervalue of 50 K to a higher value of 230 K. It is clear from the gure that the concentration dependence is almost symmetric about x=0.5. It has been discussed by Flicker and Leath [14] within the fram ework of coherent potential approximation that this asymmetry is a function of the size of the sam ple chosen i.e. a large N leads to less asymmetry. They have veried this statement by performing two calculations one for N = 100 and other for N = 2000. The concentration dependence in the later case is more symmetric as compared to the



F igure 15. (Color Online) Lattice therm al conductivity vs Pt-concentration for various tem perature T at phonon frequency = 1:05TH z.

form er ones. In our case, the results shown in Fig. 15 are the optim al symmetric structure for the concentration dependence of . This is because our calculations are performed in the reciprocal space representation which involves the entire lattice.

An interesting challenge remaining in this problem is to calculate the e ect of adding anham onicity to the model. The reason why one should be interested in calculating the anham onicity e ect is because in real systems at high temperature phonon-phonon Um klapp scattering becomes the dominant scattering mechanism. This Um klapp scattering actually arises due to the presence of anham onic terms in the H am iltonian. The e ect of this anham onicity is to atten the lattice conductivity vs concentration curve.

Fig. 16 shows the frequency dependence of di usivity D () for various alloy com positions. The thick lines on the frequency axes shows the extent of the frequency spectrum. These have been obtained from the density of states calculations presented in our rst paper on the subject [16]. It is clear from the Fig. 16 that there are basically two regions of large therm aldi usivity : one near the lower frequency region (' 0.5T Hz) and the other around a som ew hat higher frequency region (' 1.25T Hz). But as we go on increasing the Pt-concentration, the form er region of large di usivity starts decreasing gradually and becom es alm ost at for the maxim um Pt-concentration of 90%. The latter region of large di usivity sits on a portion of the frequency spectrum above the transverse acoustic vibrations. Here the modes have large velocities and are probably very e ective carriers of heat. The approximate linear decrease in di usivity starts at ' 3 THz. But the location of mobility edge in this case varies with composition in a slightly di erent way as compared to the case of NiPd alloy. Fig. 17 (bottom) shows the position of the mobility edge $_{\rm c}$ as a function of the alloy composition. As the concentration of heavy Pt increases, the band width of the frequency spectrum (which is proportional to the square root of the mass) shrinks and the position of the mobility edge within the band also shrinks. Fig. 17 (top) shows the

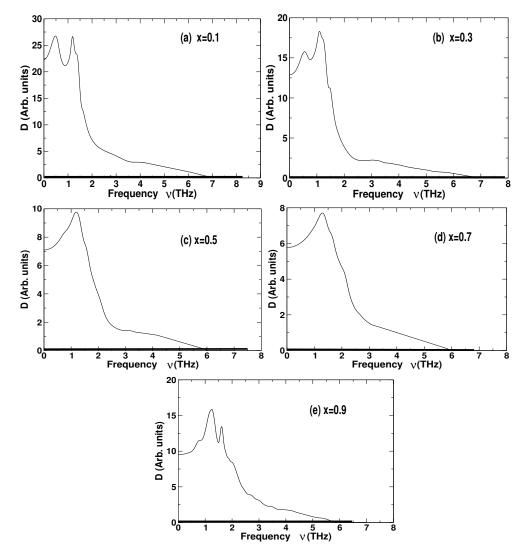
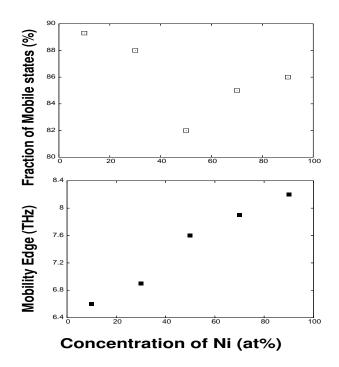


Figure 16. The con guration averaged them aldi usivities D () for N i₁ $_x$ Pt_x alloys. (a) x= 0.1; (b) x= 0.3; (c) x= 0.5; (d) x= 0.7; (e) x= 0.9. The broad line on the frequency axis shows the extent of the vibrational spectrum .

fraction of the frequency band which is extended. W hen the disorder is the strongest, i.e. at 50-50 com position, this fraction is a m inim um .

One thing is very clear from the above discussion that, in an alloy where mass disorder dom inates and the foreconstant disorder is weak (as in the case of N iP d alloy), the com plex disorder scattering processes try to localize m ore vibrationalm odes as com pared to those in an alloy where both m ass as well as the force constant disorder dom inates (as in the case of N iP t alloy). The result can be interpreted in a slightly di erent way as : \the role of force constant disorder in binary alloys is to make the vibrational eigenstates m ore delocalized ", i.e. the m ore dom inant the force constant disorder is, the m ore delocalized the vibrationalm odes will be.



F igure 17. The position of the mobility edge (bottom) and the percentage of mobile phonon states (top) as a function of the alloy composition for N iPt alloy.

In Fig.18, we present the concentration dependence of thermal di usivity for various phonon frequencies . As in NiPd, the di usivity are asymmetric about x=0.5. However this asymmetry reduces as we increase the phonon frequency. This asymmetry is relected also in the behaviour of thermal conductivity with alloy composition.

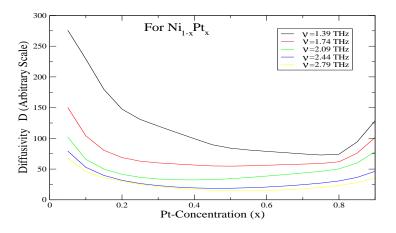


Figure 18. (Color Online) The averaged thermal diusivity D () vs Pt-concentration at various cut-o frequencies $_{\rm cutoff}$ for N i_ xPt_x alloy.

4. Conclusions

We have performed a detailed numerical study of the theoretical formulation (AM) developed earlier by us for the lattice therm al conductivity of disordered binary alloys. We have dem onstrated through our num erical results that how this multiple scattering based form alism captures the e ect of o-diagonaland environm ental disorder present in the problem . The use of augmented space method to keep track of the conquration of the system and the block recursion method have made the implementation simple yet powerful. This is rejected in the satisfaction of essential hergibits analytic property of the diagonal green function in our earlier calculation [16]. A signi cant contribution of this article beyond the earlier theoretical approaches is the inclusion of force constant uctuations properly in the theory. We have applied the form alism (AM) to two real disordered alloys; namely NiPd and NiPt. We have shown that the e ect of disorder corrections to the current and the vertex correction on the overall shape of lattice therm al conductivity for both the alloys are very sm all. Com paratively the e ect is found to be more pronounced in N iPt alloy, which is due to the presence of strong disorder both in masses and force constants in this alloy. The prominence of the force constant disorder in N iP t alloy has also been dem onstrated in the frequency dependence of lattice conductivity for various compositions of the N i_{1} xPt_x alloy. The saturation of lattice conductivity at higher temperatures has been shown for both the alloys. The concentration dependence of in N i_1 xPdx alloy has been shown to be more asymmetric about x=0.5 than in Ni_{1 x}Pt_x alloy. The numerical results on the harm onic di usivity provide an interesting idea about the localization and delocalization of the vibrational eigenstates. It says that in disordered binary alloys \ the m ore stronger the force constant disorder is, the m ore delocalized the vibrationalm odes will be". That is why N iPt alloy has larger fraction of delocalized states as com pared to that in N iP d alloy. For both the alloys, how ever we had no prior inform ation about the species dependence of the force constants but rather choose a set of force constants intuitively as we have done earlier [9, 16]. A better understanding of the role of disorder in the transport properties of random alloys could be achieved with prior information about the force constants. These could be obtained from more microscopic theories, e.g., the rst principles calculation on a set of ordered alloys. Our future endeavor would be to rectify this and attempt to obtain the dynamical matrix itself from such microscopic theories.

5. A cknow ledgem ents

O ne of the authors (A A .) would like to thank the C ouncil of Scienti c and Industrial R esearch, G ovt. of India, for a fellow ship during the time when this work was carried out.

- [1] A A lam and A . M ookerjee, P hys. Rev. B 72, 214207 (2005).
- [2] A.Mookerjee, J.Phys.C:Solid State Phys.6, L205 (1973).
- [3] C.K ittel, Phys. Rev. 75, 972 (1948); F.B rich and H.C lark, Am. J.Sci. 238, 613 (1940).
- [4] G.A. Slack, in Solid State Physics, edited by H.Ehrenreich, F.Seitz, and D.Turnbull (A cadem ic, New York, 1979), Vol. 34, p. 1.
- [5] T.Farrell and D.G reig, J.Phys.C : Solid State Phys.2, 1465 (1969).
- [6] M.Garber, B.W. Scott, and F.J.Blatt, Phys. Rev. 130, 2188 (1963); P.Lindenfeld and W.B. Pennebaker, Phys. Rev. 127, 1881 (1962).

Lattice therm al conductivity of disordered N iPd and N iPt alloys

- [7] E.Bauer, E.Gratz, G.Hut esz, and H.Muller, J.Phys.: Condens.Matter 3, 7641 (1991).
- [8] B.N. Srivastava, S.C. hatterjee, S.K. Sen, and D.K. Chakraborty, J. Phys. C : Solid State Phys. 2, S169 (1970).
- [9] A Alam and A.Mookerjee, Phys. Rev. B 71,094210 (2005).
- [10] P.G.Klemes, Proc.R.Soc.A 208, 108 (1951); Phys.Rev.119, 507 (1960).
- [11] M J.Zim an, Can.J.Phys. 34, 1256 (1956).
- [12] J.Callaway, Phys. Rev. 113, 1046 (1959).
- [13] J.E. Parrot, J. Phys. C: Solid State Phys. 2, 147 (1969).
- [14] J.K. Flicker and P.L. Leath, Phys. Rev. B 7, 2296(1973).
- [15] S.Ghosh, P.L.Leath, and M orrelH.Cohen, Phys.Rev.B 66, 214206 (2002).
- [16] A A lam and A. Mookerjee, Phys. Rev. B 69, 024205 (2004).
- [17] J.L.Feldman, M. D.Kluge, P.B.Allen, and F.W. ooten, Phys. Rev. B 48, 12589 (1993).
- [18] P.A. Lee and T.V. Ramakrishnan, Rev. Mod. Phys. 57, 287 (1985).